

AMENDMENTS TO THE CLAIMS

Claims 1-11. (Canceled).

12. (Currently Amended) An electric device comprising: a first elongated nanowire on an insulating surface and a second elongated nanowire on said insulating surface, said first nanowire having a first non-curved portion and said second nanowire having a second non-curved portion, said first non-curved portion adjacent to and at a right angle to said second non-curved portion ~~first elongated nanowire~~ and separated therefrom by a gap of between 0.4 nm and 10 nm.

13. (Original) The electric device of Claim 12 wherein said first and second nanowires form a transistor having a source, drain, and gate, and wherein said first nanowire has first and second ends; said first end of said first nanowire forming said source, said second end of said first nanowire forming said drain, and said second nanowire forming said gate.

14. (Previously Presented) The electric device of Claim 12 wherein said first elongated nanowire comprises a semiconductor chosen from the group consisting of Si, Ge, Ge_xSi_{1-x} where $0 < x < 1$, GaAs, InAs, AlGaAs, InGaAs, GaN, InN, AlN, AlGaN, and InGaN.

15. (Previously Presented) The electric device of Claim 12 wherein said gap is filled with a material that stores electrical charge.

16. (Previously Presented) The electric device of Claim 12 wherein said gap is filled with a material having electric dipole moment.

17. (Previously Presented) The electric device of Claim 12 wherein said first and second nanowires form a two-electrode memory switching device, said first nanowire forming the first electrode of said switching device and said second nanowire forming the second electrode of said switching device.

18. (Currently Amended) An electric device comprising: a first elongated nanowire on and touching an insulating surface and a second elongated nanowire on and touching the same side of said insulating surface, said first nanowire having a first straight portion and said second nanowire having a second straight portion, said first straight portion and said second straight portion forming a T-shaped structure at a right angle to said first elongated nanowire, said first and second straight portions nanowire separated by a gap of between 0.4 nm and 10 nm.

19. (Original) The electric device of Claim 18 wherein said first and second nanowires form a transistor having a source, drain, and gate, and wherein said first nanowire has first and second ends; said first end of said first nanowire forming said source, said second end of said first nanowire forming said drain, and said second nanowire forming said gate.

20. (Original) The electric device of Claim 18 wherein said first elongated nanowire comprises a semiconductor chosen from the group consisting of Si, Ge, Ge_xSi_{1-x} where $0 < x < 1$, GaAs, InAs, AlGaAs, InGaAs, GaN, InN, AlN, AlGaN, and InGaN.

21. (Original) The electric device of Claim 18 wherein said gap is filled with a material that stores electrical charge.

22. (Original) The electric device of Claim 18 wherein said gap is filled with a material having electric dipole moment.

23. (Original) The electric device of Claim 18 wherein said first and second nanowires form a two-electrode memory switching device, said first nanowire forming the first electrode of said switching device and said second nanowire forming the second electrode of said switching device.

24. (Currently Amended) An electric device comprising: a first elongated linear nanowire on an insulating surface and a second elongated linear nanowire on said insulating surface at a right angle to and in the same plane as said first elongated nanowire, said first nanowire and said second nanowire forming a T-shaped structure, said first and second nanowire separated by a gap of between 0.4 nm and 10 nm.

25. (Original) The electric device of Claim 24 wherein said first and second nanowires form a transistor having a source, drain, and gate, and wherein said first nanowire has first and second ends; said first end of said first nanowire forming said source, said second end of said first nanowire forming said drain, and said second nanowire forming said gate.

26. (Original) The electric device of Claim 24 wherein said first elongated nanowire comprises a semiconductor chosen from the group consisting of Si, Ge, Ge_xSi_{1-x} where $0 < x < 1$, GaAs, InAs, AlGaAs, InGaAs, GaN, InN, AlN, AlGaN, and InGaN.

27. (Original) The electric device of Claim 24 wherein said gap is filled with a material that stores electrical charge.

28. (Original) The electric device of Claim 24 wherein said gap is filled with a material having electric dipole moment.

29. (Original) The electric device of Claim 24 wherein said first and second nanowires form a two-electrode memory switching device, said first nanowire forming the first electrode of said switching device and said second nanowire forming the second electrode of said switching device.